## NSN 5961-01-327-1103

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Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-327-1103 **Inclosure Material:** Ceramic and metal **Overall Length:** 0.045 inches **Overall Diameter:** Between 0.075 inches and 0.086 inches **Mounting Method:** Press fit **Features Provided:** Burn in and electrostatic sensitive and hermetically sealed case **Semiconductor Material:** Silicon **Voltage Rating In Volts Per Characteristic:** 40.0 reverse voltage, peak and 60.0 reverse voltage, peak and 40.0 breakdown voltage, dc and 60.0 breakdown voltage, dc **Current Rating Per Characteristic:** 150.00 nanoamperes forward current, average peak **Power Rating Per Characteristic:** 3.0 watts small-signal input power, common-collector preset **Capacitance Rating In Picofarads:** Between 0.2 and 0.4 **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius junction **Terminal Type And Quantity:** 1 flange and 1 case Shelf Life: N/a **Unit Of Measure:** Demilitarization: No Fiig: